



# ECH8667 — P-Channel Silicon MOSFET

## General-Purpose Switching Device Applications

### Features

- ON-resistance  $R_{DS(on)1}=30m\Omega$ (typ.)
- 4V drive
- Halogen free compliance
- Protection diode in

### Specifications

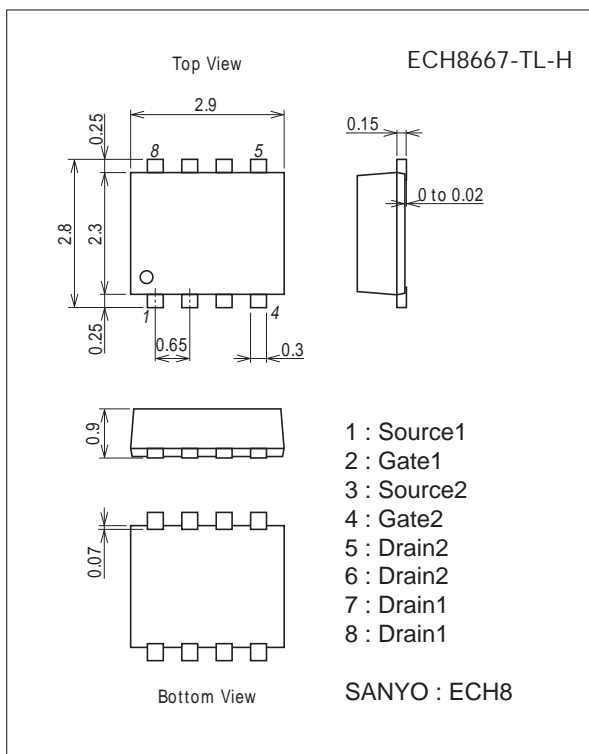
#### Absolute Maximum Ratings at $T_a=25^\circ C$

Parameter	Symbol	Conditions	Ratings	Unit
Drain-to-Source Voltage	$V_{DSS}$		-30	V
Gate-to-Source Voltage	$V_{GSS}$		$\pm 20$	V
Drain Current (DC)	$I_D$		-5.5	A
Drain Current (Pulse)	$I_{DP}$	$PW \leq 10\mu s$ , duty cycle $\leq 1\%$	-40	A
Allowable Power Dissipation	$P_D$	When mounted on ceramic substrate (900mm <sup>2</sup> ×0.8mm) 1unit	1.3	W
Total Dissipation	$P_T$	When mounted on ceramic substrate (900mm <sup>2</sup> ×0.8mm)	1.5	W
Channel Temperature	$T_{ch}$		150	°C
Storage Temperature	$T_{stg}$		-55 to +150	°C

### Package Dimensions

unit : mm (typ)

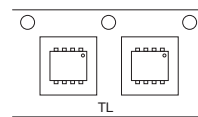
7011A-001



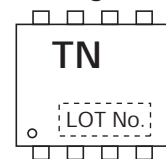
### Product & Package Information

- Package : ECH8
- JEITA, JEDEC : -
- Minimum Packing Quantity : 3,000 pcs./reel

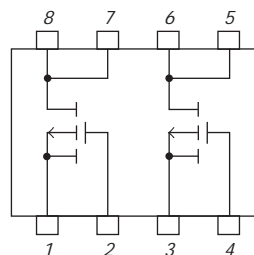
### Packing Type : TL



### Marking



### Electrical Connection

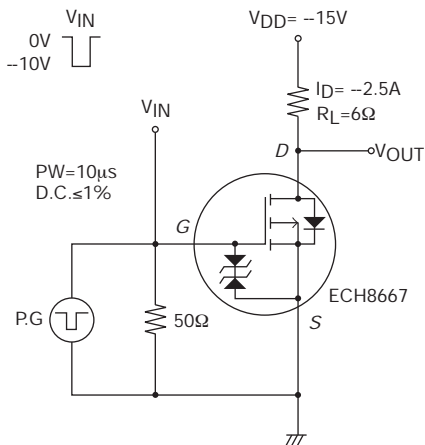


# ECH8667

## Electrical Characteristics at Ta=25°C

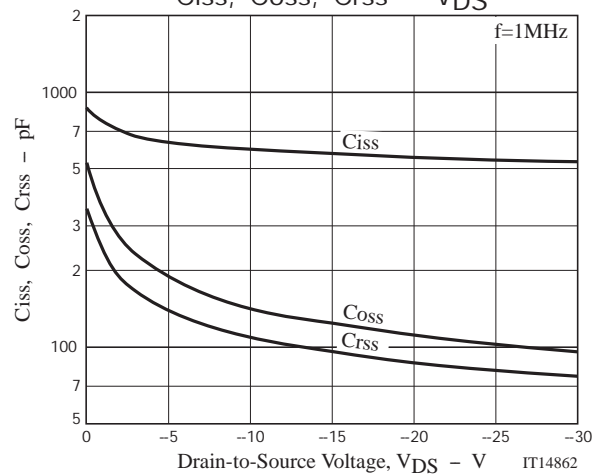
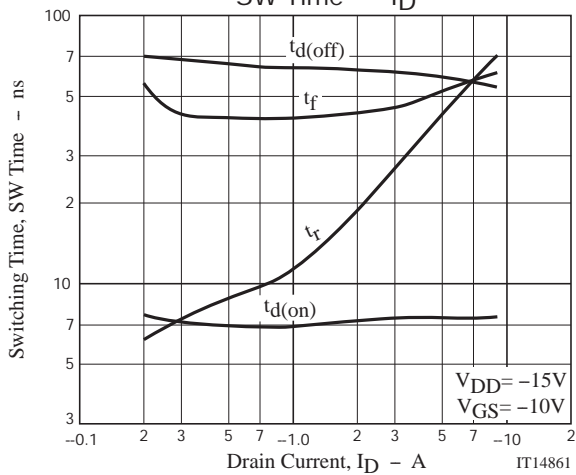
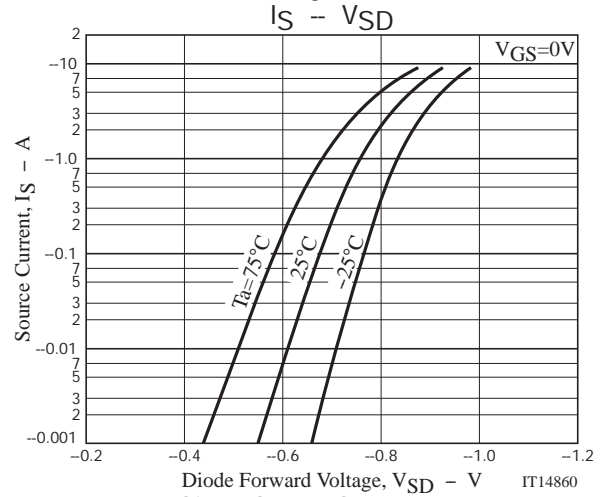
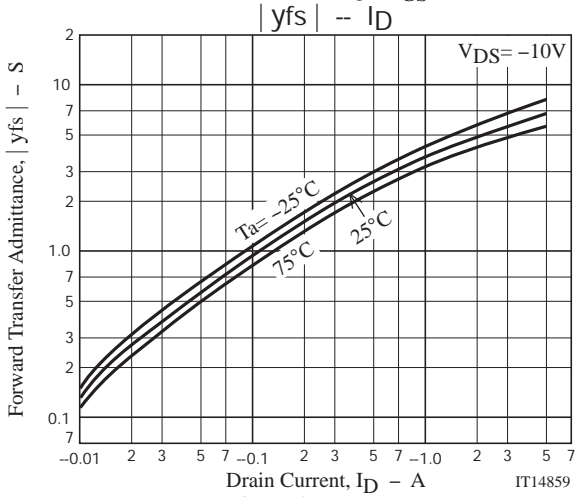
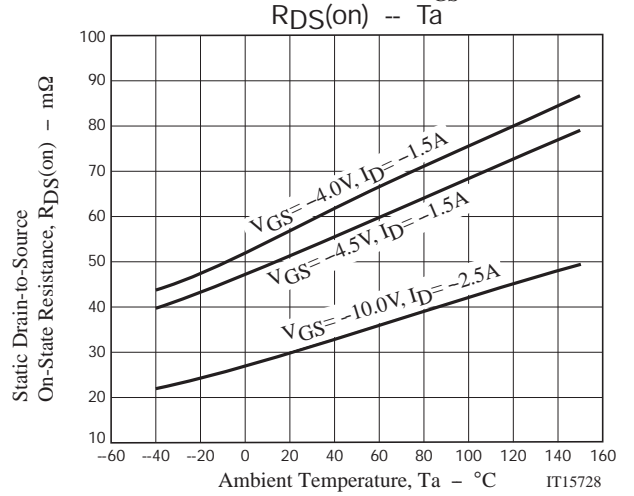
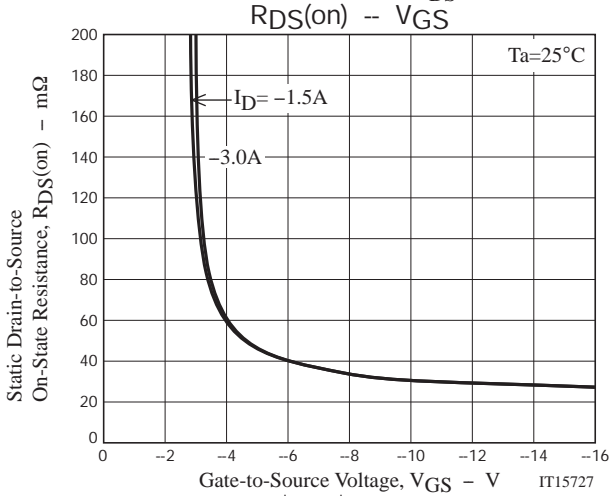
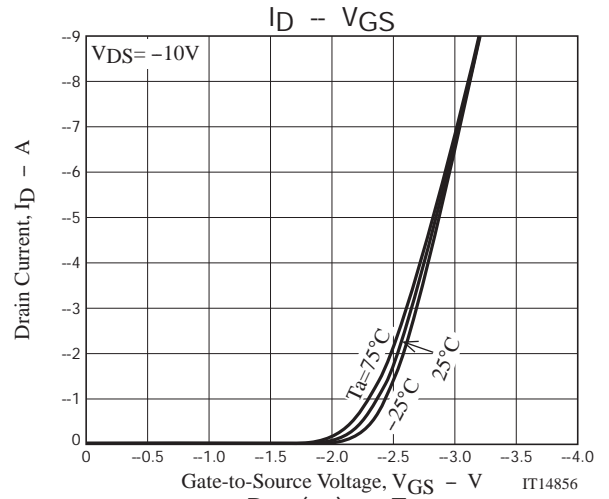
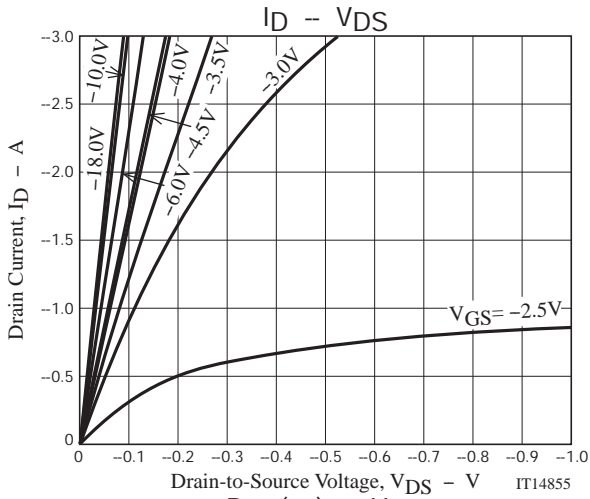
Parameter	Symbol	Conditions	Ratings			Unit
			min	typ	max	
Drain-to-Source Breakdown Voltage	V(BR)DSS	I <sub>D</sub> =-1mA, V <sub>GS</sub> =0V	-30			V
Zero-Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> =-30V, V <sub>GS</sub> =0V			-1	μA
Gate-to-Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> =±16V, V <sub>DS</sub> =0V			±10	μA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> =-10V, I <sub>D</sub> =-1mA	-1.2		-2.6	V
Forward Transfer Admittance	y <sub>fs</sub>	V <sub>DS</sub> =-10V, I <sub>D</sub> =-2.5A		5.2		S
Static Drain-to-Source On-State Resistance	R <sub>DS(on)1</sub>	I <sub>D</sub> =-2.5A, V <sub>GS</sub> =-10V		30	39	mΩ
	R <sub>DS(on)2</sub>	I <sub>D</sub> =-1.5A, V <sub>GS</sub> =-4.5V		55	77	mΩ
	R <sub>DS(on)3</sub>	I <sub>D</sub> =-1.5A, V <sub>GS</sub> =-4V		58	82	mΩ
Input Capacitance	C <sub>iss</sub>			600		pF
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> =-10V, f=1MHz		145		pF
Reverse Transfer Capacitance	C <sub>rss</sub>			110		pF
Turn-ON Delay Time	t <sub>d(on)</sub>	See specified Test Circuit.		7.2		ns
Rise Time	t <sub>r</sub>			23		ns
Turn-OFF Delay Time	t <sub>d(off)</sub>			63		ns
Fall Time	t <sub>f</sub>			42		ns
Total Gate Charge	Q <sub>g</sub>				13	
Gate-to-Source Charge	Q <sub>gs</sub>	V <sub>DS</sub> =-15V, V <sub>GS</sub> =-10V, I <sub>D</sub> =-5.5A		1.8		nC
Gate-to-Drain "Miller" Charge	Q <sub>gd</sub>			3.2		nC
Diode Forward Voltage	V <sub>SD</sub>		I <sub>S</sub> =-5.5A, V <sub>GS</sub> =0V		-0.82	-1.2

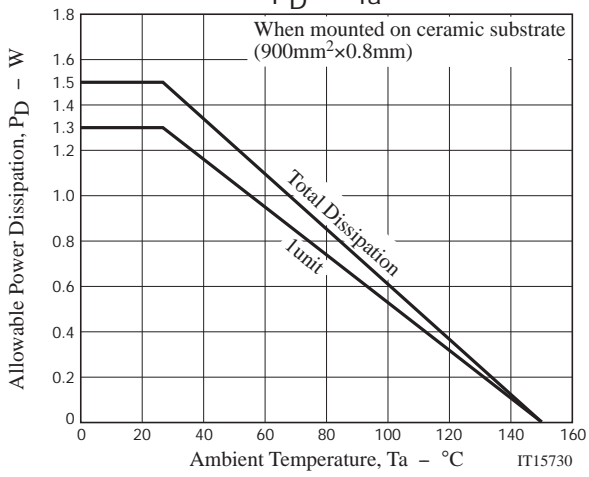
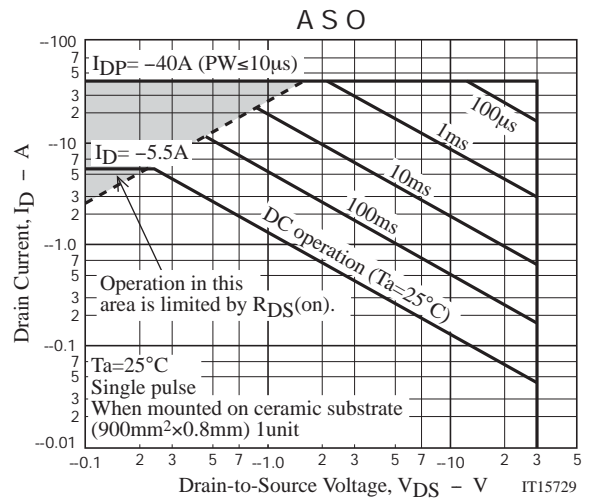
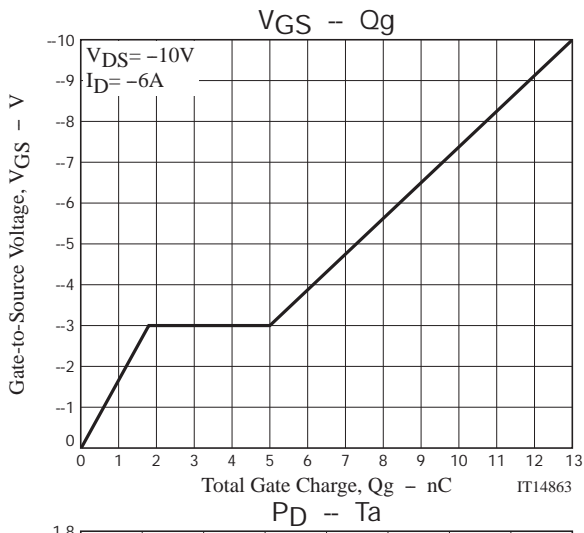
## Switching Time Test Circuit



## Ordering Information

Device	Package	Shipping	memo
ECH8667-TL-H	ECH8	3,000pcs./reel	Pb Free and Halogen Free





Embossed Taping Specification

ECH8667-TL-H

1. Packing Format

Package Name	Carrier Tape Type	Maximum Number of devices contained (pcs)			Packing format	
		Reel	Inner box	Outer box	Inner BOX (C-1)	Outer BOX (A-7)
ECH8	CPH6	3,000	15,000	90,000	5 reels contained Dimensions:mm (external) 183×72×185	6 inner boxes contained Dimensions:mm (external) 440×195×210

Reel label, Inner box label  
(unit :mm)

Outer box label

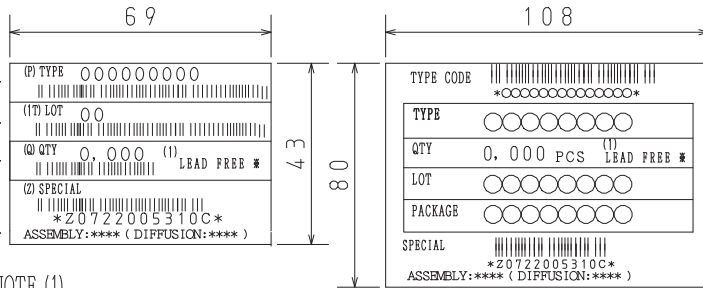
It is a label at the time of factory shipments.  
The form of a label may change in physical distribution process.

Packing method



Reel label

Type No.  
LOT No.  
Quantity  
Origin



NOTE (1)

The LEAD FREE \* description shows that the surface treatment of the terminal is lead free.

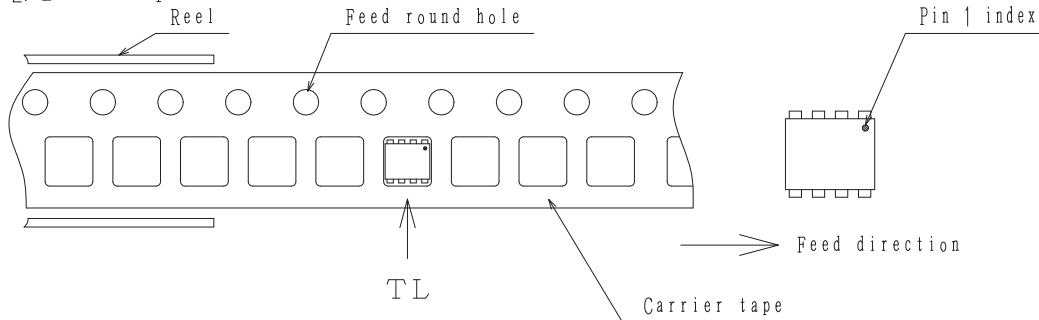
Label	JEITA Phase
LEAD FREE 3	JEITA Phase 3A
LEAD FREE 4	JEITA Phase 3

2. Taping configuration

2-1. Carrier tape size (unit:mm)

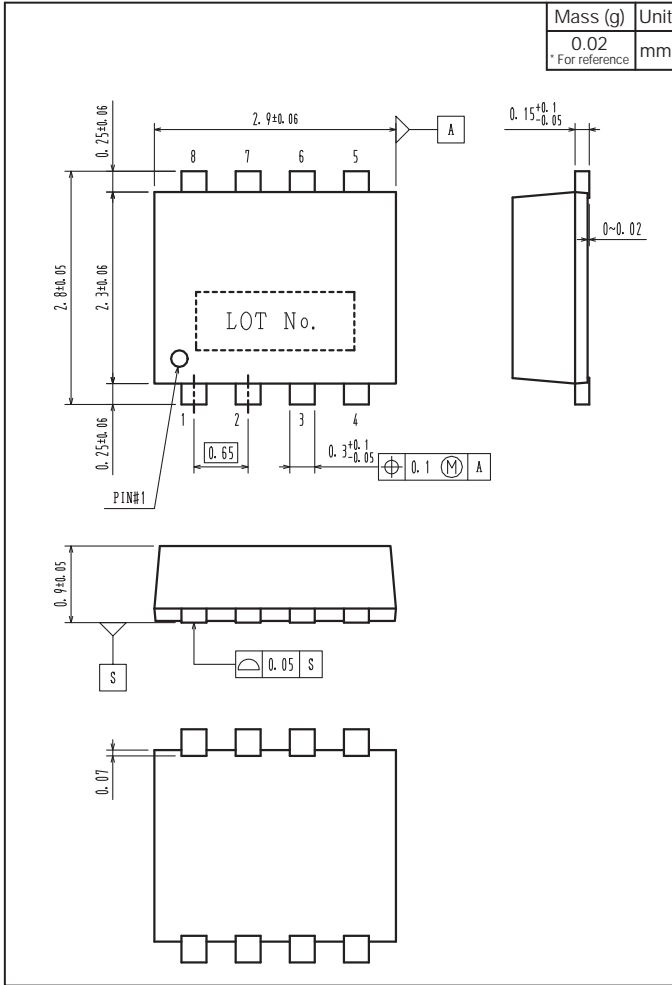


2-2. Device placement direction

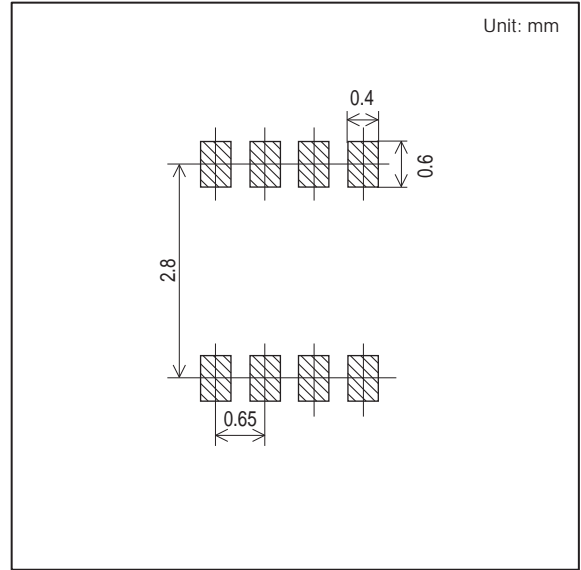


Those with pin 1 index on the feed hole side.....TL

Outline Drawing  
ECH8667-TL-H



Land Pattern Example



Note on usage : Since the ECH8667 is a MOSFET product, please avoid using this device in the vicinity of highly charged objects.

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